

L Number	Hits	Search Text	DB	Time stamp
1	312	(Sic or silicon carbide) same (acetylene or "c.sub.2H.sub.4") same (silane)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/02 14:47
2	130	(Sic or silicon carbide) same (acetylene or "c.sub.2H.sub.4") near10 (silane)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/02 14:47
3	60	(Sic or silicon carbide) near10 (acetylene or "c.sub.2H.sub.4") near10 (silane)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/02 14:48
4	19	(Sic or silicon near2 carbide) near10 (acetylene or "c.sub.2H.sub.4") near10 (silane)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/02 15:45
5	11	"1162326"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/02 15:45
6	4	"01162326"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/02 16:16
7	178	(kuniaki near2 yagi or hiroyuki near2 nagasawa).in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/02 16:16
8	43	((kuniaki near2 yagi or hiroyuki near2 nagasawa).in.) and (sic or silicon adj carbide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/02 16:17
-	674	(sic or silicon adj carbide) same surface near2 react\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/24 10:32
-	539	(sic or silicon adj carbide) near10 surface near2 react\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/24 10:32
-	115	((sic or silicon adj carbide) near10 surface near2 react\$4) same (si or silicon adj substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/24 10:34
-	45	((sic or silicon adj carbide) near10 surface near2 react\$4) near10 (sic or silicon adj carbide) near4 (layer or film) same (si or silicon adj substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/24 11:09
-	1169	(sic or silicon adj carbide) near4 (layer or film) and temperature near4 rate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/24 11:10
-	135	(sic or silicon adj carbide) near4 (layer or film) same (heat\$3 or temperature) near4 rate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/24 11:11

-	5	(sic or silicon adj carbide) near4 (layer or film) same (heat\$3 or temperature) near4 rate same rapid	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/24 11:34
-	191	(sic or silicon adj carbide) near4 (layer or film) and (heat\$3 or temperature) near4 rate near10 grow\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/24 11:36
-	31	(sic or silicon adj carbide) near4 (layer or film) and (heat\$3 or temperature) near4 rate near10 grow\$5 same (sic or silicon adj carbide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/24 11:38
-	223	(sic or silicon adj carbide) near4 (layer or film) and (heat\$3 or temperature) near2 rate same (sic or silicon adj carbide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/24 11:39
-	8	(sic or silicon adj carbide) near4 (layer or film) and (heat\$3 or temperature) near2 rate same growth near2 temperature same (sic or silicon adj carbide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/24 11:40
-	12	(sic or silicon adj carbide) near4 (layer or film) and (heat\$3 or temperature) near2 rate near5 (ramp\$4 or elevat\$4) same (sic or silicon adj carbide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/24 11:44
-	39	(heat\$3 or temperature) near2 rate near5 (ramp\$4 or elevat\$4) same (sic or silicon adj carbide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/24 11:46
-	27	((heat\$3 or temperature) near2 rate near5 (ramp\$4 or elevat\$4) same (sic or silicon adj carbide)) not ((sic or silicon adj carbide) near4 (layer or film) and (heat\$3 or temperature) near2 rate near5 (ramp\$4 or elevat\$4) same (sic or silicon adj carbide))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/24 11:44
-	61	(heat\$3) near2 rate same growth near2 temperature	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/24 11:46
-	7	(heat\$3) near2 rate same growth near2 temperature same (sic or silicon adj carbide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/24 11:47
-	474	(heat\$3) near2 rate same (sic or silicon adj carbide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/24 11:47
-	34	(heat\$3) near2 rate same (sic or silicon adj carbide) near3 (film or layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/24 11:53
-	29	"150" near5 rate same (sic or silicon adj carbide) near3 (film or layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/24 11:55
-	215	(\$3minute or \$3min) near5 rate same (sic or silicon adj carbide) near3 (film or layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/24 14:13

-	8	(\$3minute or \$3min) near5 rate near5 (heat\$4) same (sic or silicon adj carbide) near3 (film or layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/24 14:16
-	51	rate near5 (heat\$4) same (sic or silicon adj carbide) near3 (film or layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/24 14:31
-	66	rate near3 (temperature) same (sic or silicon adj carbide) near3 (film or layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/24 14:35
-	221	rapid near2 thermal same heat\$4 near2 rate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/24 14:36
-	2	rapid near2 thermal same heat\$4 near2 rate same susceptor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/24 14:37
-	24	rapid near2 thermal same heat\$4 near2 rate same product\$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/24 14:56
-	31	rapid near2 thermal same heat\$4 near2 rate same (deposit\$ or grow\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/24 15:29
-	77	rapid near2 thermal near20 (sic or silicon adj carbide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/24 15:29
-	31	rapid near2 thermal near20 (sic or silicon adj carbide) near4 (layer or film)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/24 15:29
-	67	(silicon or si) near2 substrate and (RTP or rapid adj thermal near2 process\$5) near3 rate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/03/01 15:46
-	3	(sic or silicon adj carbide) near2 (film or layer) and (RTP or rapid adj thermal near2 process\$5) near3 rate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/03/01 15:48
-	4	(sic or silicon adj carbide) same (RTP or rapid adj thermal near2 process\$5) near3 rate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/03/01 15:48
-	673	(sic or silicon adj carbide) same (heat\$3 or ramp\$4 or elevat\$4) near5 rate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/03/01 15:50
-	50	(sic or silicon adj carbide) same (heat\$3 or ramp\$4 or elevat\$4) near5 rate near10 (rapid\$3 or fast\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/03/01 15:53

-	2	4855254.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/01 16:00
-	2	reactor same rapid near2 thermal near10 rate same substrate	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/01 16:01
-	16	reactor same rapid near2 thermal near10 rate	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/01 16:24
-	23	tungsten near2 halogen near2 lamp near10 (rate)	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/01 16:26